The RF Line

PNP Silicon High-Frequency Transistor

. . . designed for amplifier, oscillator or frequency multiplier applications in industrial equipment. Suitable for use as a Class A, B or C output driver or pre–driver stages in VHF and UHF.

- Low Cost SORF Plastic Surface Mount Package
- Guaranteed RF Specification — $|S_{21}|^2$
- S–Parameter Characterization
- Tape and Reel Packaging Options Available by adding suffix:
  R1 suffix = 500 units per reel
  R2 suffix = 2,500 units per reel

MRF5583

I_C = –500 mA
SURFACE MOUNT
HIGH–FREQUENCY
TRANSISTOR
PNP SILICON

CASE 751–05, STYLE 1
(SO–8)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	–30	V
Collector–Base Voltage	V_{CBO}	–30	V
Emitter–Base Voltage	V_{EBO}	–3.0	V
Collector Current — Continuous	I_C	–500	mA
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150	°C

DEVICE MARKING

MRF5583 = 5583

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	1.0 8.0	Watt mW/°C
Storage Temperature	T_{stg}	150	°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	°C/W

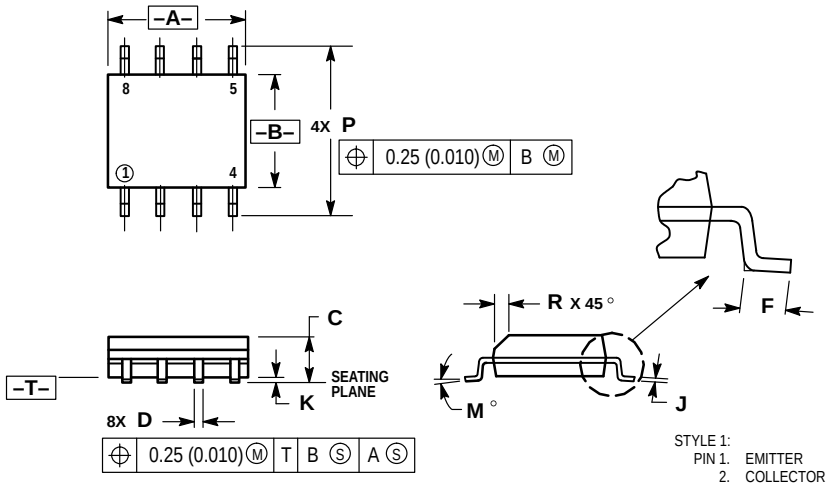
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (I_C = –10 mA)	$V_{(BR)CEO}$	–30	—	—	V
Collector–Base Breakdown Voltage (I_C = –10 μA)	$V_{(BR)CBO}$	–30	—	—	V
Emitter–Base Breakdown Voltage (I_E = –100 μA)	$V_{(BR)EBO}$	–3	—	—	V
Collector Cutoff Current (V_{CB} = –20 V)	I_{CBO}	—	—	–1.0	μA
Emitter Cutoff Current (V_{EB} = –2.0 V)	I_{EBO}	—	—	–0.5	μA
ON CHARACTERISTICS					
DC Current Gain (I_C = –40 mA, V_{CE} = –2.0 V) (I_C = –100 mA, V_{CE} = –2.0 V) (I_C = –300 mA, V_{CE} = –5.0 V)	h_{FE}	20 25 15	— — —	— 100 —	—
Collector–Emitter Saturation Voltage (I_C = –100 mA, I_B = –10 mA)	$V_{CE(sat)}$	—	—	0.8	V
Base–Emitter On Voltage (I_C = –100 mA, V_{CE} = –2.0 V)	$V_{BE(on)}$	—	—	1.8	V
SMALL–SIGNAL CHARACTERISTICS					
Current–Gain — Bandwidth Product (I_C = –35 mA, V_{CE} = –15 V, f = 100 MHz)	f_T	—	2100	—	MHz
Insertion Gain (V_{CE} = –15 V, I_C = –35 mA, f = 250 MHz)	$\|S_{21}\|^2$	12.5	15.5	—	dB

V_{CE} (Volts)	I_C (mA)	f (MHz)	S_{11}		S_{21}		S_{12}		S_{22}	
			$\|S_{11}\|$	ϕ	$\|S_{21}\|$	ϕ	$\|S_{12}\|$	ϕ	$\|S_{22}\|$	ϕ
–15	–35	10	0.47	–57	64.7	155	0.01	60	0.83	–26
		30	0.59	–116	42.2	126	0.02	44	0.56	–58
		50	0.63	–140	28.8	113	0.02	39	0.39	–74
		70	0.64	–151	21.4	105	0.02	42	0.30	–82
		100	0.65	–161	15.4	97	0.02	45	0.24	–80
		300	0.67	179	5.23	79	0.05	58	0.13	–109
		500	0.67	168	3.11	66	0.07	60	0.20	–114
		700	0.67	160	2.24	57	0.09	60	0.24	–116
		1000	0.66	146	1.54	44	0.13	60	0.30	–123

Table 1. Common Emitter S–Parameters

PACKAGE DIMENSIONS



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.196
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.18	0.25	0.007	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7 °	0 °	7 °
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

STYLE 1:
PIN 1. EMITTER
2. COLLECTOR
3. COLLECTOR
4. EMITTER
5. EMITTER
6. BASE
7. BASE
8. EMITTER

CASE 751–05
ISSUE M

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